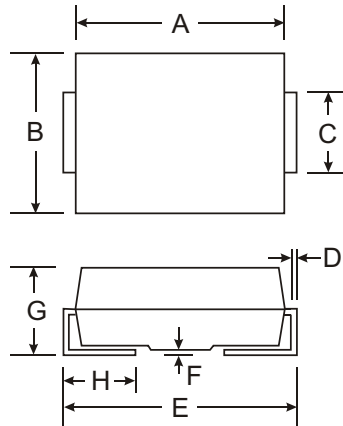


### Features

- 100A Peak Pulse Current @ 10/1000 s
- 400A Peak Pulse Current @ 8/20 s
- 58 - 320V Stand-Off Voltages
- Oxide-Glass Passivated Junction
- Bi-Directional Protection In a Single Device
- High Off-State impedance and Low On-State Voltage

### Mechanical Data

- Case: SMB, Molded Plastic
- Plastic Material: UL Flammability Classification Rating 94V-0
- Moisture sensitivity: Level 1 per J-STD-020A
- Terminals: Solder Plated Terminal - Solderable per MIL-STD-202, Method 208
- Polarity: None; Bi-Directional Devices Have No Polarity Indicator
- Weight: 0.093 grams (approx.)
- Marking: Date Code & Marking Code (See Page 4)
- Ordering Information: See Page 4



SMB		
Dim	Min	Max
A	4.06	4.57
B	3.30	3.94
C	1.96	2.21
D	0.15	0.31
E	5.21	5.59
F	0.05	0.20
G	2.01	2.62
H	0.76	1.52
All Dimensions in mm		

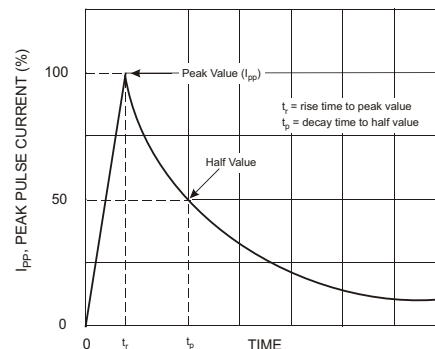
### Maximum Ratings @ T<sub>A</sub> = 25 C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load.  
For capacitive load, derate current by 20%.

Characteristic	Symbol	Value	Unit
Non-Repetitive Peak Impulse Current @ 10/1000us	I <sub>pp</sub>	100	A
Non-Repetitive Peak On-State Current @ 8.3ms (one-half cycle)	I <sub>TSM</sub>	50	A
Junction Temperature Range	T <sub>j</sub>	-40 to +150	C
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	C
Thermal Resistance, Junction to Lead	R <sub>JL</sub>	20	°C/W
Thermal Resistance, Junction to Ambient	R <sub>JA</sub>	100	°C/W
Typical Positive Temperature Coefficient for Breakdown Voltage	VBR/ T <sub>j</sub>	0.1	%/°C

### Maximum Rated Surge Waveform

Waveform	Standard	I <sub>pp</sub> (A)
2/10 us	GR-1089-CORE	500
8/20 us	IEC 61000-4-5	400
10/160 us	FCC Part 68	250
10/700 us	ITU-T, K20/K21	200
10/560 us	FCC Part 68	160
10/1000 us	GR-1089-CORE	100

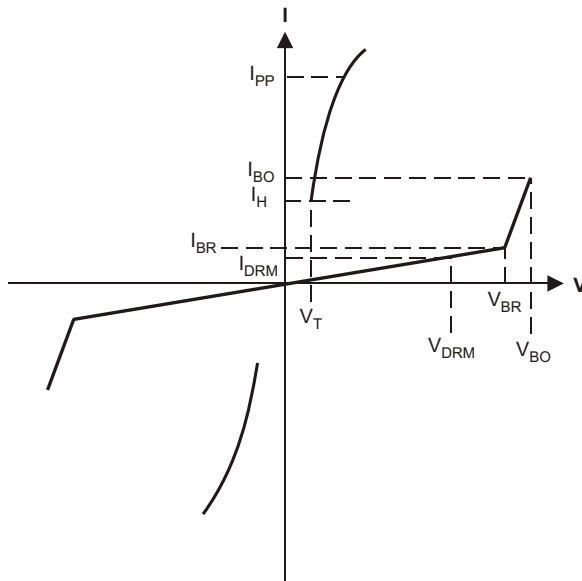


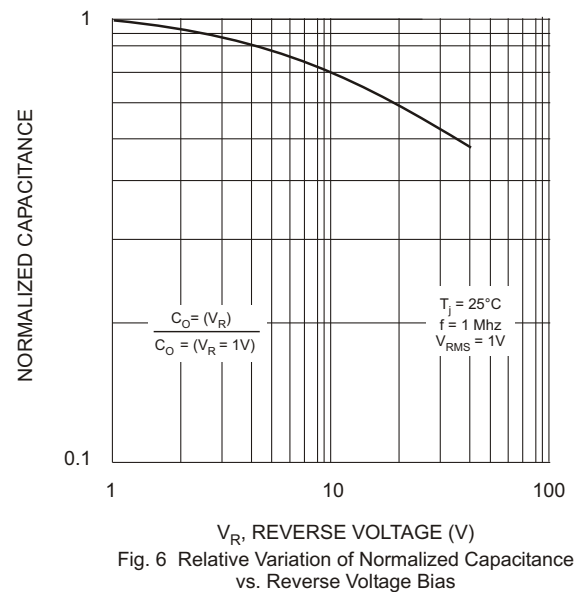
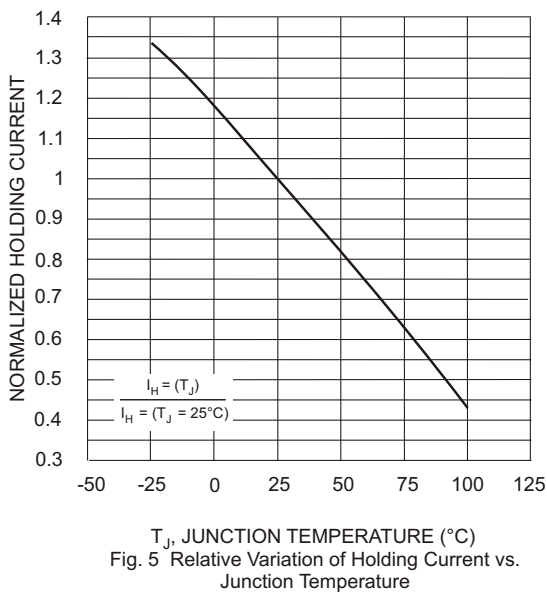
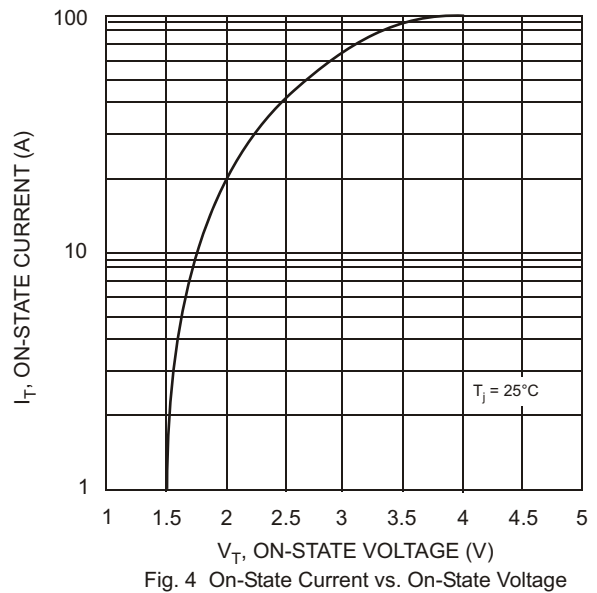
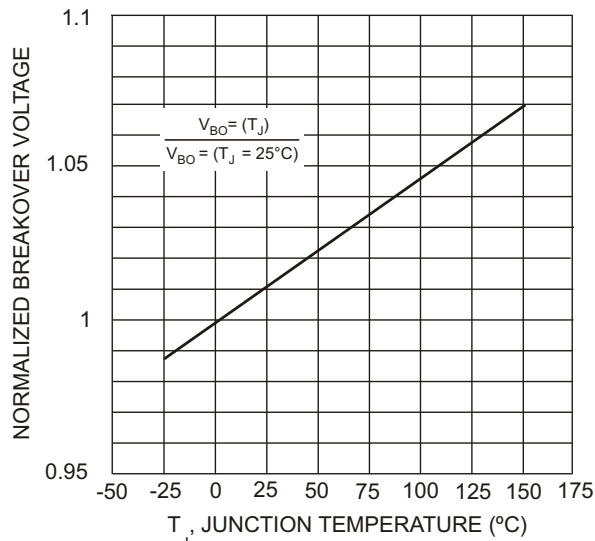
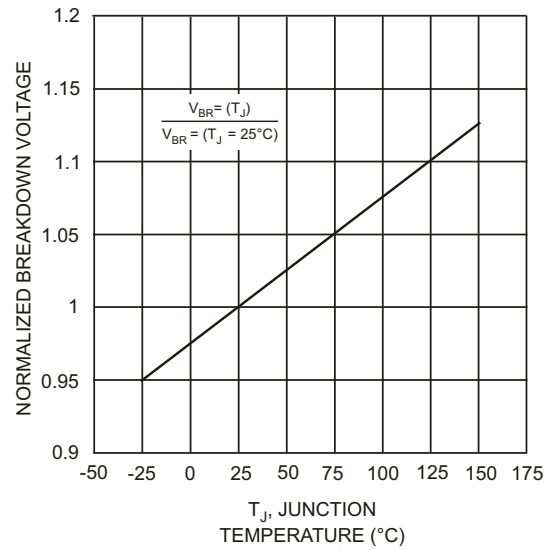
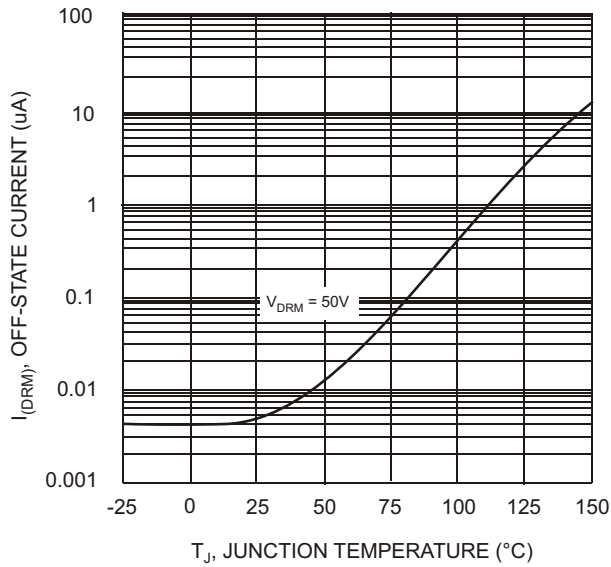
**Electrical Characteristics** @  $T_A = 25\text{ C}$  unless otherwise specified

Part Number	Rated Repetitive Off-State Voltage	Off-State Leakage Current @ $V_{DRM}$	Breakover Voltage	On-State Voltage @ $I_T = 1\text{ A}$	Breakover Current $I_{BO}$		Holding Current $I_H$		Off-State Capacitance	Marking Code
	$V_{DRM}$ (V)	$I_{DRM}$ ( $\mu\text{A}$ )	$V_{BO}$ (V)	$V_T$ (V)	Min (mA)	Max (mA)	Min (mA)	Max (mA)	$C_O$ (pF)	
TB0640H	58	5	77	3.5	50	800	150	800	200	T064H
TB0720H	65	5	88	3.5	50	800	150	800	200	T072H
TB0900H	75	5	98	3.5	50	800	150	800	200	T090H
TB1100H	90	5	130	3.5	50	800	150	800	120	T110H
TB1300H	120	5	160	3.5	50	800	150	800	120	T130H
TB1500H	140	5	180	3.5	50	800	150	800	120	T150H
TB1800H	160	5	220	3.5	50	800	150	800	120	T180H
TB2300H	190	5	265	3.5	50	800	150	800	80	T230H
TB2600H	220	5	300	3.5	50	800	150	800	80	T260H
TB3100H	275	5	350	3.5	50	800	150	800	80	T310H
TB3500H	320	5	400	3.5	50	800	150	800	80	T350H

Symbol	Parameter
$V_{DRM}$	Stand-off Voltage
$I_{DRM}$	Leakage current at stand-off voltage
$V_{BR}$	Breakdown voltage
$I_{BR}$	Breakdown current
$V_{BO}$	Breakover voltage
$I_{BO}$	Breakover current
$I_H$	Holding current <span style="float: right;">NOTE: 1</span>
$V_T$	On state voltage
$I_{PP}$	Peak pulse current
$C_O$	Off-state capacitance <span style="float: right;">NOTE: 2</span>

- Notes:
- $I_H > (V_L/R_L)$  If this criterion is not obeyed, the TSPD triggers but does not return correctly to high-resistance state. The surge recovery time does not exceed 30ms.
  - Off-state capacitance measured at  $f = 1.0\text{ MHz}$ ,  $1.0V_{RMS}$  signal,  $V_R = 2V_{DC}$  bias.

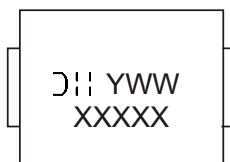




**Ordering Information** (Note 3)

Device	Packaging	Shipping
TB0640H-13 TB0720H-13 TB0900H-13 TB1100H-13 TB1300H-13 TB1500H-13 TB1800H-13 TB2300H-13 TB2600H-13 TB3100H-13 TB3500H-13	SMB	3000/Tape & Reel

Notes: 3. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

**Marking Information**

XXXXX = Product Type Marking Code  
YWW = Date Code Marking  
Y = Year ex: 2 = 2002  
WW = Week

Date Code Key

Year	2002	2003	2004
Code	2	3	4